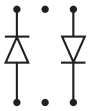
CMKD3003DO

SURFACE MOUNT
DUAL, ISOLATED, OPPOSING
LOW LEAKAGE SILICON
SWITCHING DIODES

ULTRAmini™



SOT-363 CASE

Central Semiconductor Corp.

www.centralsemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMKD3003DO contains two (2) Isolated Opposing Silicon Switching Diodes, manufactured by the epitaxial planar process, epoxy molded in a ULTRAmini™ surface mount package. These devices are designed for switching applications requiring extremely low leakage.

MARKING CODE: C303

MAXIMUM RATINGS: (T_A=25°C)	**SYMBOL**		**UNITS**
Continuous Reverse Voltage	V_R	180	V
Average Rectified Current	I_O	200	mA
Continuous Forward Current	I_F	600	mA
Peak Repetitive Forward Current	I_{FRM}	700	mA
Peak Forward Surge Current, tp=1.0μs	I_{FSM}	2.0	A
Peak Forward Surge Current, tp=1.0s	I_{FSM}	1.0	A
Power Dissipation	P_D	350	mW
Operating and Storage Junction Temperature	T_J, T_{stg}	-65 to +150	°C
Thermal Resistance	Θ_{JA}	357	°C/W

ELECTRICAL CHARACTERISTICS PER DIODE: (T_A=25°C unless otherwise noted)

SYMBOL	**TEST CONDITIONS**	**MIN**	**MAX**	**UNITS**
I_R	V_R=125V		1.0	nA
I_R	V_R=125V, T_A=150°C		3.0	μA
I_R	V_R=180V		10	nA
I_R	V_R=180V, T_A=150°C		5.0	μA
BV_R	I_R=5.0μA	200		V
V_F	I_F=1.0mA	0.62	0.72	V
V_F	I_F=10mA	0.72	0.83	V
V_F	I_F=50mA	0.80	0.89	V
V_F	I_F=100mA	0.83	0.93	V
V_F	I_F=200mA	0.87	1.10	V
V_F	I_F=300mA	0.90	1.15	V
C_T	V_R=0, f=1.0MHz		4.0	pF

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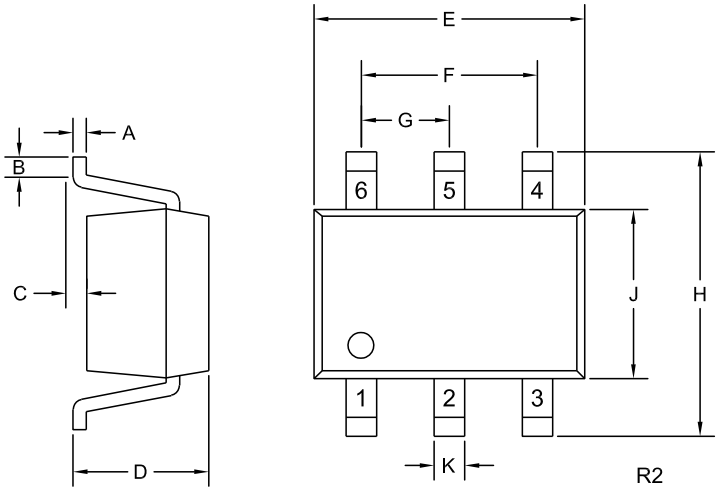
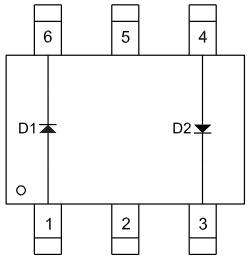
SOT-363 CASE - MECHANICAL OUTLINE



PIN CONFIGURATION



LEAD CODE:
1) Anode D1
2) NC
3) Cathode D2
4) Anode D2
5) NC
6) Cathode D1

MARKING CODE: C303

DIMENSIONS				
	INCHES		MILLIMETERS	
SYMBOL	MIN	MAX	MIN	MAX
A	0.004	0.010	0.10	0.25
B	0.005	-	0.12	-
C	0.000	0.004	0.00	0.10
D	0.031	0.043	0.80	1.10
E	0.071	0.087	1.80	2.20
F	0.051		1.30	
G	0.026		0.65	
H	0.075	0.091	1.90	2.30
J	0.043	0.055	1.10	1.40
K	0.006	0.012	0.15	0.30

SOT-363 (REV: R2)